

## **KSC5026M**

## High Voltage and High Reliability

- High Speed Switching
- Wide SOA



10-126

1. Emitter 2.Collector 3.Base

## **NPN Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	1100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current (DC)	1.5	А
I <sub>CP</sub>	Collector Current (Pulse)	5	А
I <sub>B</sub>	Base Current	0.8	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	1100			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 5 \text{mA}, I_{B} = 0$	800			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage $I_C = 0.75A$ $I_{B1} = -I_{B2} = 0.15A$ L = 5mH, Clamped		800			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 800V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.1A$ $V_{CE} = 5V, I_{C} = 0.5A$	10 8	N W W	40	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 0.75A, I_B = 0.15A$			2	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 0.75A$ , $I_B = 0.15A$			1.5	V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		35		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.1A$		15		MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 400V			0.5	μs
t <sub>STG</sub>	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 1A$			3	μs
t <sub>F</sub>	Fall Time	$R_L = 400\Omega$			0.3	μs

## h<sub>FE</sub> Classification

Classification	N	R	0
h <sub>FE1</sub>	10 ~ 20	15 ~ 30	20 ~ 40

## **Typical Characteristics**

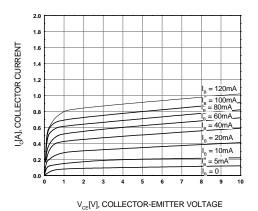


Figure 1. Static Characteristic

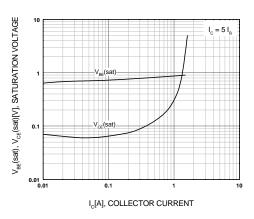


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

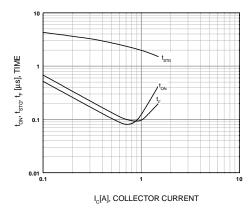


Figure 5. Switching Time

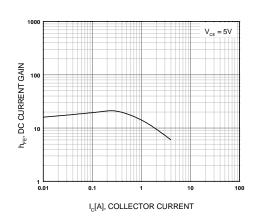


Figure 2. DC current Gain

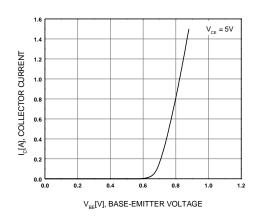


Figure 4. Base-Emitter On Voltage

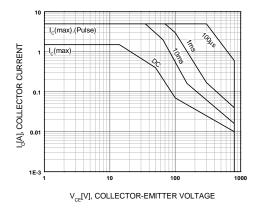


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

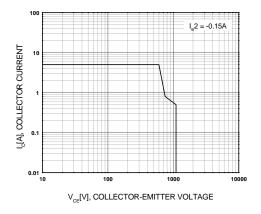


Figure 7. Reverse Bias Safe Operating Area

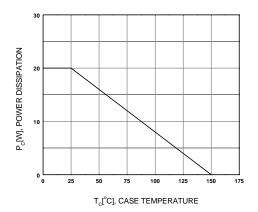
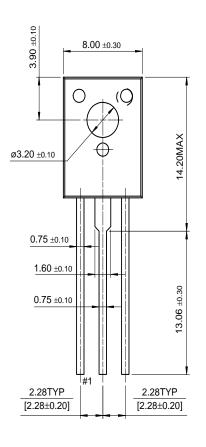
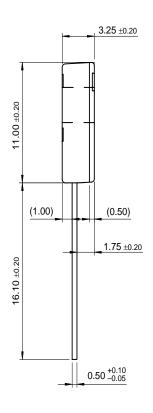


Figure 8. Power Derating

# **Package Dimensions**

TO-126







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
$CROSSVOLT^{TM}$	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	$QS^{TM}$	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E2CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™ _
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